

# **PS9924**

HIGH CMR, 10 Mbps OPEN COLLECTOR OUTPUT TYPE, 8-PIN LSDIP PHOTOCOUPLER FOR CREEPAGE DISTANCE OF 14.5 mm

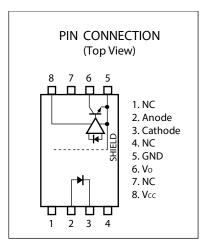
R08DS0059EJ0200 Rev.2.00 Feb 12, 2020

#### DESCRIPTION

The PS9924 is an optical coupled high-speed, active low type isolator containing an AlGaAs LED on the input side and a photodiode and a signal processing circuit on the output side on one chip.

#### **FEATURES**

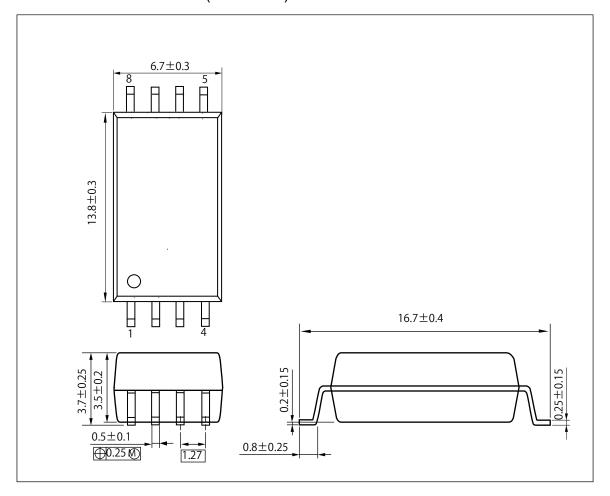
- Long creepage distance (14.5 mm MIN.)
- High common mode transient immunity (CM<sub>H</sub>, CM<sub>L</sub> =  $\pm 15$  kV/ $\mu$ s MIN.)
- High-speed response (tphl = 100 ns MAX., tplh = 100 ns MAX.)
- Low power consumption (V<sub>CC</sub> = 3.3/5V)
- 8-pin LSDIP (Long Creepage SDIP) type
- Embossed tape product: PS9924-F3: 1 000 pcs/reel
- Pb-Free and Halogen Free product
- · Safety standards
  - UL approved: UL1577, Double protection
  - CSA approved: CAN/CSA-C22.2 No.62368-1, Reinforced insulation
  - SEMKO approved: EN 62368-1, IEC 62368-1, Reinforced insulation
  - VDE approved: DIN EN 60747-5-5 (Option)



### **APPLICATIONS**

- Industrial inverter
- Solar inverter

# PACKAGE DIMENSIONS (UNIT: mm)

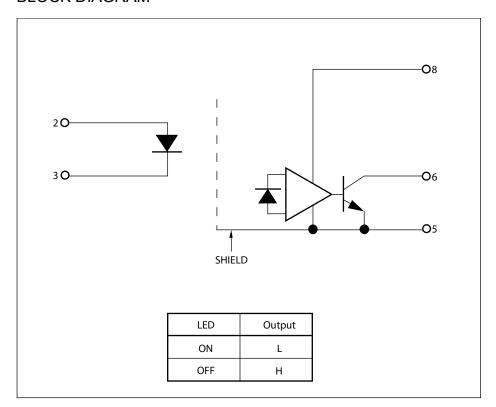


Weight: 0.642g (typ.)

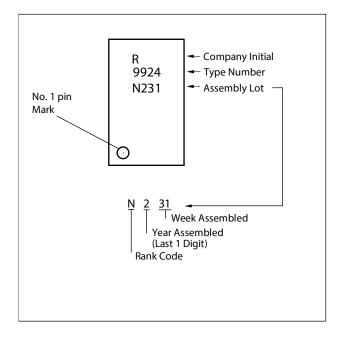
# PHOTOCOUPLER CONSTRUCTION

Parameter	MIN.
Air Distance	14.5 mm
Creepage Distance	14.5 mm
Isolation Distance	0.4 mm

# **BLOCK DIAGRAM**



# MARKING EXAMPLE



### ORDERING INFORMATION

Part Number	Order Number	Solder Plating Specification	Packing Style	Safety Standard Approval	Application Part Number <sup>*1</sup>
PS9924	PS9924-Y-AX	Pb-Free and	10 pcs (Tape 10 pcs cut)	Standard products	PS9924
PS9924-F3	PS9924-Y-F3-AX	Halogen Free	Embossed Tape 1 000	(UL, CSA, SEMKO	
		(Ni/Pd/Au)	pcs/reel	approved)	
PS9924-V	PS9924-Y-V-AX		10 pcs (Tape 10 pcs cut)	UL, CSA, SEMKO,	
PS9924-V-F3	PS9924-Y-V-F3-AX		Embossed Tape 1 000	DIN EN 60747-5-5	
			pcs/reel	approved	

Note: \*1. For the application of the Safety Standard, following part number should be used.

# ABSOLUTE MAXIMUM RATINGS (T<sub>A</sub> = 25°C, unless otherwise specified)

Parameter		Symbol	Ratings	Unit
Diode	Forward Current	l <sub>F</sub>	25	mA
	Reverse Voltage	V <sub>R</sub>	5	V
	Power Dissipation*1	P <sub>D</sub>	45	mW
Detector	Supply Voltage	Vcc	7	V
	Output Voltage	Vo	7	V
	Output Current	lo	25	mA
	Power Dissipation *2	Pc	250	mW
Isolation Voltage*3		BV	7 500	Vr.m.s.
Operating Ambient Temperature		TA	-40 to +110	°C
Storage Temperature		T <sub>stg</sub>	−55 to +125	°C

Notes: \*1. Reduced to 0.8 mW/°C at T<sub>A</sub> = 85°C or more.

### RECOMMENDED OPERATING CONDITIONS

Parameter	Symbol	MIN.	TYP.	MAX.	Unit
Low Level Forward Voltage	V <sub>F(OFF)</sub>	-2		0.8	V
High Level Forward Current	I <sub>F(ON)</sub>	8	10	12	mA
Supply Voltage	Vcc	2.7		5.5	V
Pull-up Resistor	R∟	330		4k	Ω

<sup>\*2.</sup> Reduced to 5.2 mW/°C at T<sub>A</sub> = 85°C or more.

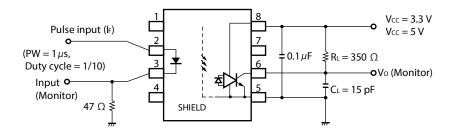
<sup>\*3</sup> AC voltage for 1 minute at  $T_A$  = 25°C, RH = 60% between input and output. Pins 1-4 shorted together, 5-8 shorted together.

# ELECTRICAL CHARACTERISTICS ( $T_A = -40$ to +110°C, unless otherwise specified)

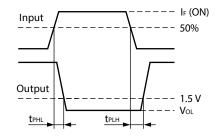
$ \begin{array}{ c c c c c } \hline Reverse Current & I_R & V_R = 3 \ V, T_A = 25^\circ C & 30 \\ \hline Terminal Capacitance & C_t & f = 1 \ MHz, \ V_F = 0 \ V, \ T_A = 25^\circ C & 30 \\ \hline \hline Detector & High Level Output Current & I_OH & V_CC = V_O = 3.3 \ V, \ V_F = 0.8 \ V & 1 & 1 & 1 \\ \hline V_CC = V_O = 3.3 \ V, \ I_F = 10 \ mA, & 0.2 & 0 \\ \hline V_{CC} = 5.5 \ V, \ I_F = 10 \ mA, & 0.2 & 0.2 \\ \hline V_{CC} = 5.5 \ V, \ I_F = 10 \ mA, & 0.2 & 0.2 \\ \hline V_{CC} = 5.5 \ V, \ I_F = 10 \ mA, & 0.2 & 0.2 \\ \hline V_{CC} = 5.5 \ V, \ I_F = 10 \ mA, & 0.2 & 0.2 \\ \hline V_{CC} = 5.5 \ V, \ I_F = 10 \ mA, & 0.2 & 0.2 \\ \hline V_{CC} = 5.5 \ V, \ I_F = 10 \ mA, & 0.2 & 0.2 \\ \hline V_{CC} = 5.5 \ V, \ I_F = 10 \ mA, & 0.2 & 0.2 \\ \hline V_{CC} = 5.5 \ V, \ I_F = 10 \ mA, & 0.2 & 0.2 \\ \hline V_{CC} = 5.5 \ V, \ I_F = 10 \ mA, & 0.2 & 0.2 \\ \hline V_{CC} = 5.5 \ V, \ I_F = 10 \ mA, & 0.2 & 0.2 \\ \hline V_{CC} = 5.5 \ V, \ I_F = 10 \ mA, & 0.2 & 0.2 \\ \hline V_{CC} = 5.5 \ V, \ I_F = 10 \ mA, & 0.2 & 0.2 \\ \hline V_{CC} = 5.5 \ V, \ I_F = 10 \ mA, & 0.2 & 0.2 \\ \hline V_{CC} = 5.5 \ V, \ I_F = 10 \ mA, & 0.2 & 0.2 \\ \hline V_{CC} = 5.5 \ V, \ I_F = 10 \ mA, & $	X. Unit	MAX.	TYP.*1	MIN.	ditions	Cor	Symbol	Parameter	
$ \begin{array}{ c c c c } \hline \text{Terminal Capacitance} & C_{i} & f = 1  \text{MHz},  V_{F} = 0  \text{V},  T_{A} = 25^{\circ}\text{C} & 30 & 10 & 10 & 10 & 10 & 10 & 10 & 10$	3 V	1.8	1.56	1.3			V <sub>F</sub>	Forward Voltage	Diode
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	μΑ	10					I <sub>R</sub>	Reverse Current	
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	pF		30		= 0 V, T <sub>A</sub> = 25°C	f = 1 MHz, V <sub>F</sub>	Ct	Terminal Capacitance	
$ \begin{array}{ c c c c } \hline Low Level Output Voltage & V_{OL} & V_{CC} = 3.3 \ V, \  _F = 10 \ mA, \  _{OL} = 13 \ mA \\ \hline Voc = 5.5 \ V, \  _F = 10 \ mA, \  _{OL} = 13 \ mA \\ \hline Voc = 5.5 \ V, \  _F = 0 \ mA, \  _{OL} = 13 \ mA \\ \hline Voc = 5.5 \ V, \  _F = 0 \ mA, \  _{OL} = 13 \ mA \\ \hline Voc = 5.5 \ V, \  _F = 0 \ mA, \  _{OL} = 13 \ mA \\ \hline Voc = 0 \ mA, \  _{OL} = 13 \ mA \\ \hline Voc = 0 \ mA, \  _{OL} = 10 \ mA, \  _{O$	μA	80	1		$V_{F} = 0.8 V$			High Level Output Current	Detector
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	כ	100	1		$V_{F} = 0.8 V$	$V_{CC} = V_0 = 5.5$			
$ \begin{array}{ c c c c } \hline & Vcc = 5.5 \ V, \   F = 10 \ mA, \\ &  _{OL} = 13 \ mA \\ \hline \\ Vcc = 3.3 \ V, \  _{F} = 0 \ mA, \\ & V_{O} = open \\ \hline \\ Vcc = 5.5 \ V, \  _{F} = 0 \ mA, \\ & V_{O} = open \\ \hline \\ Vcc = 5.5 \ V, \  _{F} = 0 \ mA, \\ & V_{O} = open \\ \hline \\ Vcc = 5.5 \ V, \  _{F} = 10 \ mA, \\ & V_{O} = open \\ \hline \\ Vcc = 5.5 \ V, \  _{F} = 10 \ mA, \\ & V_{O} = open \\ \hline \\ Vcc = 5.5 \ V, \  _{F} = 10 \ mA, \\ & V_{O} = open \\ \hline \\ Vcc = 5.5 \ V, \  _{F} = 10 \ mA, \\ & V_{O} = open \\ \hline \\ Vcc = 5.5 \ V, \  _{F} = 10 \ mA, \\ & V_{O} = open \\ \hline \\ Vcc = 5.5 \ V, \  _{F} = 10 \ mA, \\ & V_{O} = open \\ \hline \\ Vcc = 5.5 \ V, \  _{F} = 10 \ mA, \\ & V_{O} = open \\ \hline \\ Vcc = 5.0 \ V, R_{L} = 350 \ \Omega, \\ & V_{O} = 0.8 \ V \\ \hline \\ Vcc = 5.0 \ V, R_{L} = 350 \ \Omega, \\ & V_{O} = 0.8 \ V \\ \hline \\ Vcc = 5.0 \ V, R_{L} = 350 \ \Omega, \\ & V_{O} = 0.8 \ V \\ \hline \\ Vcc = 5.0 \ V, R_{L} = 350 \ \Omega, \\ & V_{O} = 1 \ MHz, \\ & V_{O} = 1 \ MHz, \\ & V_{O} = 1 \ MHz, \\ & V_{O} = 3.3 \ V, \\ & I_{F} = 10 \ mA, \\ & R_{L} = 350 \ \Omega, \\ & V_{L} = 10 \ mA, \\ & R_{L} = 350 \ \Omega, \\ & V_{L} = 10 \ mA, \\ & R_{L} = 350 \ \Omega, \\ & V_{L} = 10 \ mA, \\ & R_{L} = 350 \ \Omega, \\ & V_{L} = 10 \ mA, \\ & V_{L} = 3.0 \ V, \\ & V_{C} = 3.3 \ $	6 V	0.6	0.2		= 10 mA,	V <sub>CC</sub> = 3.3 V, I <sub>I</sub>	V <sub>OL</sub>	Low Level Output Voltage	
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $						I <sub>OL</sub> = 13 mA			
$ \begin{array}{ c c c c c } \hline High Level Supply Current & I_{CCH} & V_{CC} = 3.3 \text{ V, } I_F = 0 \text{ mA,} \\ V_O = \text{ open} & V_{CC} = 5.5 \text{ V, } I_F = 0 \text{ mA,} \\ V_O = \text{ open} & 3 & 3 & 3 & 3 & 3 & 3 & 3 & 3 & 3 & $					= 10 mA,				
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$									
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	mA	7	2		= 0 mA,		Іссн	High Level Supply Current	
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	_								
		7	3		= 0 mA,				
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$		40			10 1				
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	) mA	10	4		= 10 mA,		ICCL	Low Level Supply Current	
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	<del></del>	10	E		- 10 m A				
$ \begin{array}{ c c c c }\hline \text{Coupled} & \text{Threshold Input Voltage} \\ (H \to L) & & & & & & & & & & & & & & & & & \\ \hline (H \to L) & & & & & & & & & & & & & & & & \\ \hline (H \to L) & & & & & & & & & & & & & & & \\ \hline (H \to L) & & & & & & & & & & & & & & & \\ \hline (H \to L) & & & & & & & & & & & & & & & \\ \hline & & & &$		10	3		- 10 IIIA,				
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	mA	5	2		. = 350 O		Icui	Threshold Innut Voltage	Coupled
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$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$					ι = 350 Ω.			(1. / 2)	
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$					_				
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	Ω			10 <sup>11</sup>	RH = 40 to 60%		R <sub>I-O</sub>	Isolation Resistance	
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	pF		1.0					Isolation Capacitance	
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$					,			•	
$R_{L} = 350 \ \Omega, \\ C_{L} = 15 \ pF \\ V_{CC} = 5 \ V, \\ I_{F} = 10 \ mA, \\ R_{L} = 350 \ \Omega, \\ C_{L} = 15 \ pF \\ T_{A} = -40^{\circ}C \ to \\ T_{A} = 25^{\circ}C \\ 45 \ 7 \\ T_{A} = -40^{\circ}C \ to \\ T_{A} = 25^{\circ}C \\ T_{A} = 25^{\circ}C \\ T_{A} = 25^{\circ}C \\ T_{A} = 25^{\circ}C \\ T_{A} = -40^{\circ}C \ to \\ T_{A} = -40^{\circ}C \ to \\ T_{A} = -40^{\circ}C \ to \\ T_{A} = 25^{\circ}C \\ T_{A$	ns	75	45		T <sub>A</sub> = 25°C	V <sub>CC</sub> = 3.3 V,	t <sub>PHL</sub>	Propagation Delay Time	
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$						$I_F = 10 \text{ mA},$		$(H \rightarrow L)^{*2}$	
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	5	100			$T_A = -40^{\circ}C$ to	$R_L = 350 \Omega$ ,			
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$					110°C	C <sub>L</sub> = 15 pF			
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	;	75	45		T <sub>A</sub> = 25°C	Vcc = 5 V,			
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$						$I_F = 10 \text{ mA},$			
Propagation Delay Time $(L \to H)^{*2}$ $t_{PLH}$ $V_{CC} = 3.3 \text{ V}, t_{F} = 10 \text{ mA}, t_{PL} = 350 \Omega, t_{PL} = 100 \text{ mA}, t_{PL} = 350 \Omega, t_{PL} = 100 \text{ mA}, t_{PL} = 350 \Omega, t_{PL} = -400 \text{ C to} t_{PL} = 100 \text{ mA}, t_{PL} = 350 \Omega, t_{PL} = -400 \text{ C to} t_{PL} = 100 \text{ mA}, t_{PL} = 350 \Omega, t_{PL} = -400 \text{ C to} t_{PL} = 100 \text{ mA}, t_{PL} = 100 \text{ mA}, t_{PL} = 350 \Omega, t_{PL} = -400 \text{ C to} t_{PL} = 100 \text{ mA}, t_{PL} = 100 \text{ mA}, t_{PL} = 350 \Omega, t_{PL} = -400 \text{ C to} t_{PL} = 100 \text{ mA}, t_{PL} $	כ	100			$T_A = -40$ °C to	$R_L = 350 \Omega$ ,			
$ \begin{array}{cccccccccccccccccccccccccccccccccccc$					110°C	C <sub>L</sub> = 15 pF			
$\begin{array}{cccccccccccccccccccccccccccccccccccc$	ns	75	40		T <sub>A</sub> = 25°C	$V_{CC} = 3.3 V$ ,	tplH	Propagation Delay Time	
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$						$I_F = 10 \text{ mA},$		$(L \rightarrow H)^{*2}$	
$V_{CC} = 5 \text{ V}, \qquad T_A = 25^{\circ}\text{C} \qquad \qquad 40 \qquad 7$ $I_F = 10 \text{ mA}, \qquad \qquad T_A = -40^{\circ}\text{C to} \qquad \qquad 11$	5	100			$T_A = -40^{\circ}C$ to	$R_L = 350 \Omega$ ,			
$I_F = 10 \text{ mA},$ $R_L = 350 \Omega,$ $T_A = -40^{\circ}\text{C to}$ 10					110°C	C <sub>L</sub> = 15 pF			
$R_L = 350 \ \Omega,$ $T_A = -40^{\circ} C \text{ to}$ 10		75	40		T <sub>A</sub> = 25°C	Vcc = 5 V,			
						$I_F = 10 \text{ mA},$			
	)	100							
						·			
Pulse Width Distortion $  t_{PHL} - t_{PLH}   V_{CC} = 3.3/5 \text{ V}, I_F = 10 \text{ mA},$ (PWD)*2 $  t_{PHL} - t_{PLH}   V_{CC} = 3.3/5 \text{ V}, I_F = 10 \text{ mA},$ 5	ns	35	5		· ·		t <sub>PHL-</sub> t <sub>PLH</sub>		
Propagation Delay t <sub>psk</sub>		40			- 1		t <sub>psk</sub>	Propagation Delay	
Skew*2			0.0						
Rise Time*2 t <sub>r</sub> 20									Fall Time*2
			_						
Common Mode $CM_H$ $V_{CC} = 3.3/5 \text{ V}, I_F = 0 \text{ mA}, 15 20$	kV/μs		20	15	· ·		СМн		
Transient Immunity at $V_0 > 2 \text{ V}, R_L = 350 \Omega,$					·			1	
High Level Output*3	10.11			45			C		
	kV/μs		20	15	•				
Transient Immunity at $V_0 < 0.8 \text{ V}, R_L = 350 \Omega,$ Low Level Output <sup>*3</sup> $V_{CM} = 1 \text{ kV}, T_A = 25^{\circ}\text{C}$					· ·	· ·			

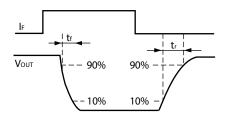
# Notes: \*1. Typical values at T<sub>A</sub> = 25°C

### \*2. Test circuit for propagation delay time

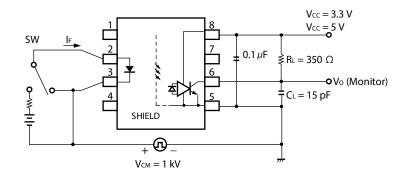


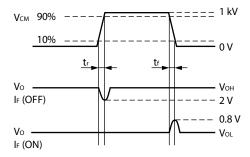
Remark CL includes probe and stray wiring capacitance.





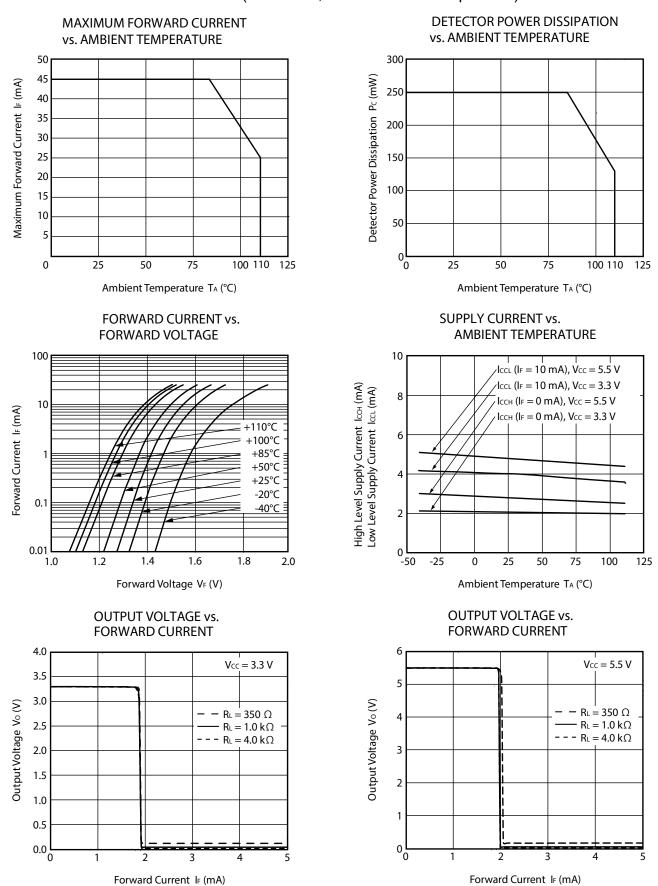
### \*3. Test circuit for common mode transient immunity





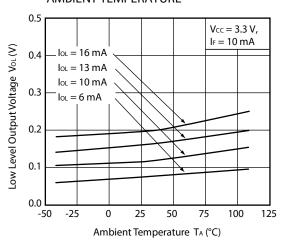
Remark CL includes probe and stray wiring capacitance.

# TYPICAL CHARACTERISTICS (T<sub>A</sub> = 25°C, unless otherwise specified)

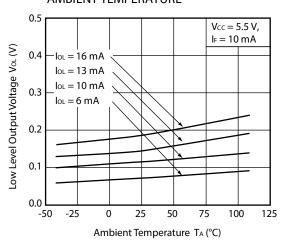


Remark The graphs indicate nominal characteristics.

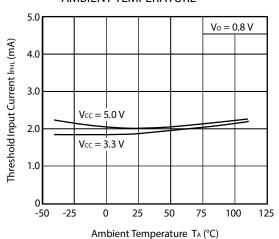
# LOW LEVEL OUTPUT VOLTAGE vs. AMBIENT TEMPERATURE



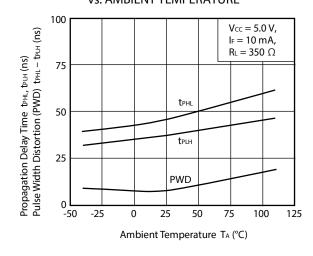
# LOW LEVEL OUTPUT VOLTAGE vs. AMBIENT TEMPERATURE



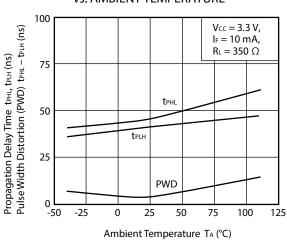
# THRESHOLD INPUT CURRENT vs. AMBIENT TEMPERATURE



### PROPAGATION DELAY TIME, PULSE WIDTH DISTORTION vs. AMBIENT TEMPERATURE

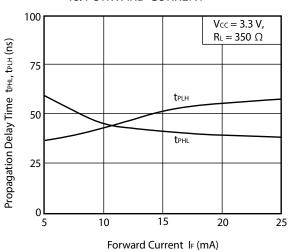


#### PROPAGATION DELAY TIME, PULSE WIDTH DISTORTION vs. AMBIENT TEMPERATURE

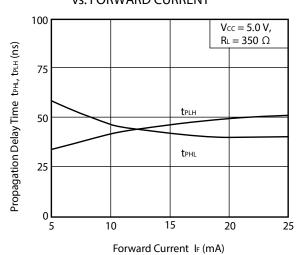


Remark The graphs indicate nominal characteristics.

# PROPAGATION DELAY TIME vs. FORWARD CURRENT

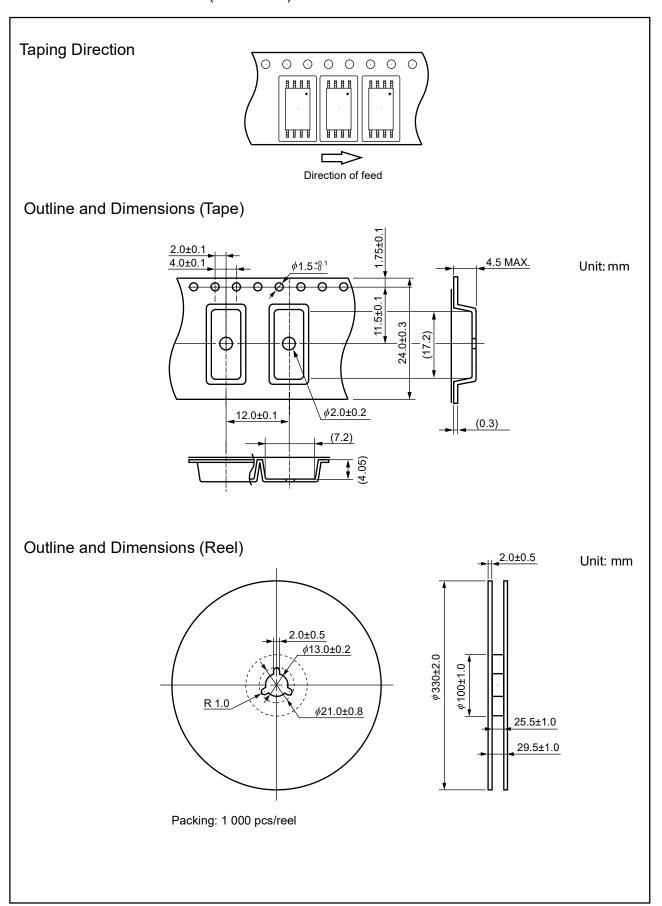


# PROPAGATION DELAY TIME vs. FORWARD CURRENT

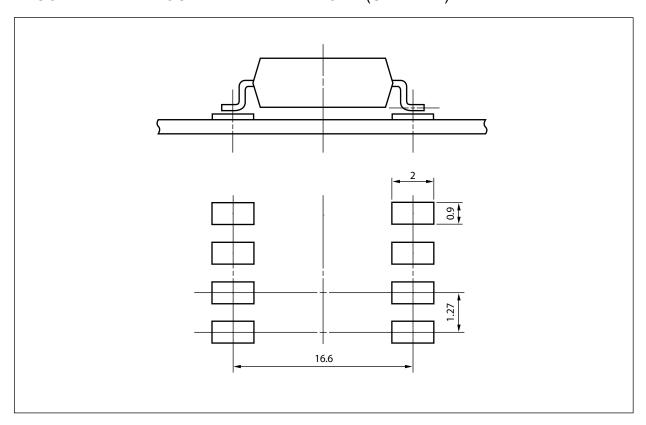


Remark The graphs indicate nominal characteristics.

# TAPING SPECIFICATIONS (UNIT: mm)



# RECOMMENDED MOUNT PAD DIMENSIONS (UNIT: mm)



Remark All dimensions in this figure must be evaluated before use.

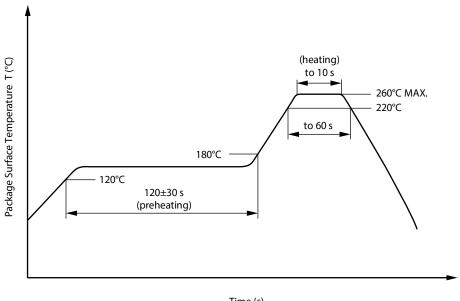
### NOTES ON HANDLING

- 1. Recommended soldering conditions
  - (1) Infrared reflow soldering
    - Peak reflow temperature 260°C or below (package surface temperature)
    - Time of peak reflow temperature 10 seconds or less Time of temperature higher than 220°C 60 seconds or less
    - Time to preheat temperature from 120 to 180°C 120±30 s
    - Number of reflows Three
    - Flux Rosin flux containing small amount of chlorine (The

flux with a maximum chlorine content of 0.2 Wt% is

recommended.)

### Recommended Temperature Profile of Infrared Reflow



Time (s)

#### (2) Wave soldering

Temperature 260°C or below (molten solder temperature)

10 seconds or less

Preheating conditions 120°C or below (package surface temperature)

Number of times One (Allowed to be dipped in solder including plastic mold portion.) Flux

Rosin flux containing small amount of chlorine (The flux with a maximum

chlorine content of 0.2 Wt% is recommended.)

### (3) Soldering by Soldering Iron

350°C or below Peak Temperature (lead part temperature) Time (each pins) 3 seconds or less

Flux Rosin flux containing small amount of chlorine

(The flux with a maximum chlorine content of 0.2 Wt% is recommended.)

- (a) Soldering of leads should be made at the point 1.5 to 2.0 mm from the root of the lead
- (b) Please be sure that the temperature of the package would not be heated over 100°C

#### (4) Cautions

Flux Cleaning

Avoid cleaning with Freon based or halogen-based (chlorinated etc.) solvents.

Do not use fixing agents or coatings containing halogen-based substances.

### 2. Cautions regarding noise

Be aware that when voltage is applied suddenly between the photocoupler's input and output at startup, the output transistor may enter the on state, even if the voltage is within the absolute maximum ratings.

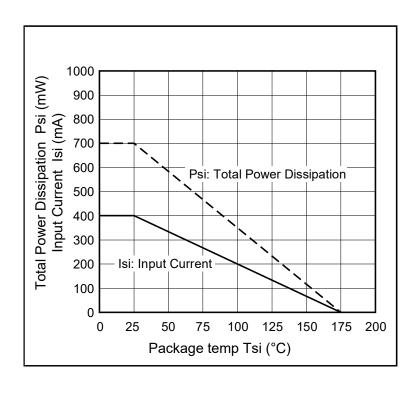
### **USAGE CAUTIONS**

- 1. This product is weak for static electricity by designed with high-speed integrated circuit so protect against static electricity when handling.
- 2. By-pass capacitor of more than 0.1  $\mu$ F is used between V<sub>CC</sub> and GND near device. Also, ensure that the distance between the leads of the photocoupler and capacitor is no more than 10 mm.
- 3. Pin 1, 4 (which is an NC\*1 pin) can either be connected directly to the GND pin on the LED side or left open.
  - Also, Pin 7 (which is an NC\*1 pin) can either be connected directly to the GND pin on the detector side or left open. Unconnected pins should not be used as a bypass for signals or for any other similar purpose because this may degrade the internal noise environment of the device.
  - Note: \*1. NC: Non-Connection (No Connection).
- 4. Avoid storage at a high temperature and high humidity.

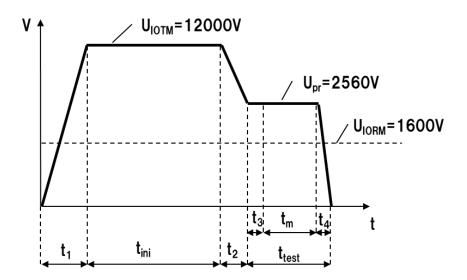
# SPECIFICATION OF VDE MARKS LICENSE DOCUMENT

Parameter	Symbol	Rating	Unit
Climatic test class (IEC 60068-1/DIN EN 60068-1)		40/110/21	
Dielectric strength maximum operating isolation voltage Test voltage (partial discharge test, procedure a for type test and random test) $U_{pr} = 1.6 \times U_{IORM.},  P_d < 5  pC$	U <sub>IORM</sub> U <sub>pr</sub>	1 600 2 560	V <sub>peak</sub> V <sub>peak</sub>
Test voltage (partial discharge test, procedure b for all devices) $U_{pr} = 1.875 \times U_{IORM.},  P_d < 5 \; pC$	U <sub>pr</sub>	3 000	V <sub>peak</sub>
Highest permissible overvoltage	Uютм	12 000	V <sub>peak</sub>
Degree of pollution (IEC 60664-1/DIN EN 60664-1 (VDE 0110-1))		2	
Comparative tracking index (IEC 60112/DIN EN 60112 (VDE 0303-11))	CTI	175	
Material group (IEC 60664-1/DIN EN 60664-1 (VDE 0110-1))		III a	
Storage temperature range	$T_{stg}$	-55 to +125	°C
Operating temperature range	TA	-40 to +110	°C
Isolation resistance, minimum value $V_{IO}$ = 500 V dc at $T_A$ = 25°C $V_{IO}$ = 500 V dc at $T_A$ MAX. at least 100°C	Ris MIN. Ris MIN.	10 <sup>12</sup> 10 <sup>11</sup>	Ω Ω
Safety maximum ratings (maximum permissible in case of fault, see thermal derating curve) Package temperature Current (input current I <sub>F</sub> , Psi = 0) Power (output or total power dissipation)	Tsi Isi Psi	175 400 700	°C mA mW
Isolation resistance V <sub>IO</sub> = 500 V dc at T <sub>A</sub> = Tsi	Ris MIN.	10 <sup>9</sup>	Ω

# Dependence of maximum safety ratings with package temperature

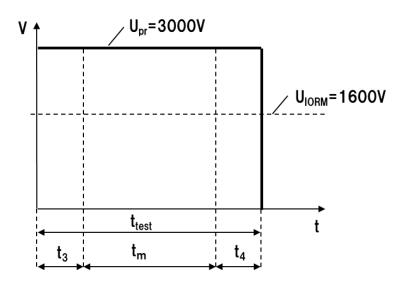


Method A Destructive Test, Type and Sample test



 $t_1,t_2$ =1 to 10 sec  $t_3,t_4$ =1 sec  $t_{m (PARTIAL DISCHARGE)}$ =10 sec  $t_{test}$ =12 sec  $t_{ini}$ =60 sec

# Method b Non-destructive Test, 100% Production Test



 $t_{3}, t_{4} = 0.1 \text{ sec} \\ t_{m \; (PARTIAL \; DISCHARGE)} = 1.0 \text{ sec} \\ t_{test} = 1.2 \text{ sec}$ 

#### Caution

GaAs Products

This product uses gallium arsenide (GaAs).

GaAs vapor and powder are hazardous to human health if inhaled or ingested, so please observe the following points.

- Follow related laws and ordinances when disposing of the product. If there are no applicable laws and/or ordinances, dispose of the product as recommended below.
  - Commission a disposal company able to (with a license to) collect, transport and dispose of materials that contain arsenic and other such industrial waste materials.
- 2. Exclude the product from general industrial waste and household garbage, and ensure that the product is controlled (as industrial waste subject to special control) up until final disposal.
- Do not burn, destroy, cut, crush, or chemically dissolve the product.
- Do not lick the product or in any way allow it to enter the mouth.

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